

**AMENDMENTS TO THE CLAIMS**

This listing of claims replaces all prior listing of claims in this application.

Claims 1-25 (canceled).

26. (currently amended) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition ~~comprising~~ consisting of:

a flowing plasma etchant mixture consisting ~~essentially~~ of at least one fluorocarbon and ammonia, ~~wherein the a flow rate ratio of each fluorocarbon to ammonia is from about 2:1 to about 40:1.~~

27. (previously presented) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of fluorohydrocarbons, chlorofluorocarbons and chlorofluorohydrocarbons.

28. (original) The composition of claim 27, wherein said fluorocarbon is at least one member selected from the group consisting of C<sub>4</sub>F<sub>8</sub>, C<sub>4</sub>F<sub>6</sub>, C<sub>5</sub>F<sub>8</sub>, CF<sub>4</sub>, C<sub>2</sub>F<sub>6</sub>, C<sub>3</sub>F<sub>8</sub>, CHF<sub>3</sub>, and CH<sub>2</sub>F<sub>2</sub>.

29. (original) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of CF<sub>4</sub>, CHF<sub>3</sub>, and CH<sub>2</sub>F<sub>2</sub>.

30. (original) The composition of claim 29, wherein said fluorocarbon is at least two members selected from the group consisting of CF<sub>4</sub>, CHF<sub>3</sub>, and CH<sub>2</sub>F<sub>2</sub>.

31. (original) The composition of claim 30, wherein said fluorocarbon is a combination of CF<sub>4</sub>, CHF<sub>3</sub>, and CH<sub>2</sub>F<sub>2</sub>.

32. (previously presented) The composition of claim 26, wherein said composition is ineffective to remove side wall spacers of a gate stack formed over said substrate.

Claims 33-70 (canceled).

71. (currently amended) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition ~~comprising~~ consisting of:

a ~~flowing~~ plasma etchant mixture ~~comprising at least~~ consisting of at least two fluorocarbons  $\text{CF}_4$  and  $\text{NH}_3$ , ~~wherein the flow rate ratio of said  $\text{CF}_4$ : $\text{NH}_3$  is greater than about 3:1.~~

Claims 72-76 (canceled).

77. (new) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition consisting of:

a gaseous etchant mixture consisting of at least one fluorocarbon and ammonia.